

Silicon PNP Power Transistors

2SA1133 2SA1133A

DESCRIPTION

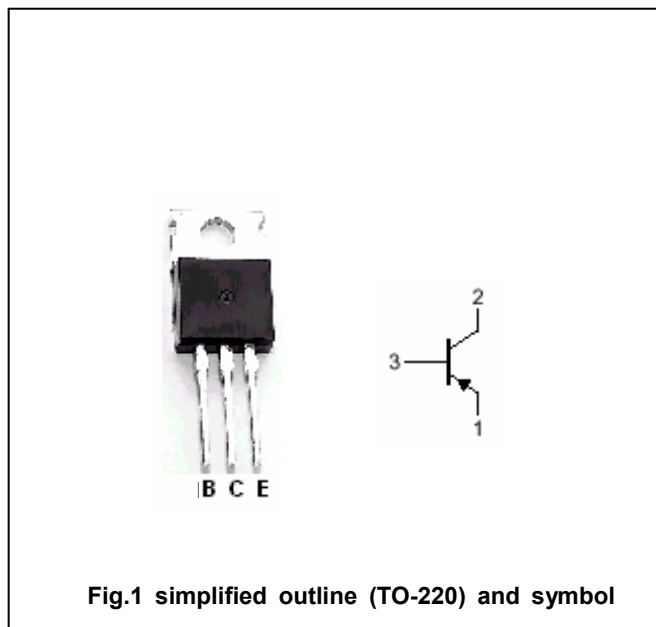
- With TO-220 package
- High breakdown voltage
- High power dissipation
- Complement to type 2SC2660/2660A

APPLICATIONS

- For power amplifier and TV vertical deflection output applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage		Open emitter	-200	V
V_{CEO}	Collector-emitter voltage	2SA1133	Open base	-150	V
		2SA1133A		-180	
V_{EBO}	Emitter-base voltage		Open collector	-6	V
I_C	Collector current			-2.0	A
I_{CM}	Collector current-peak			-3.0	A
P_T	Total power dissipation		$T_C=25^\circ\text{C}$	30	W
T_j	Junction temperature			150	$^\circ\text{C}$
T_{stg}	Storage temperature			-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SA1133	$I_C=-5mA, I_B=0$	-150			V
		2SA1133A		-180			
$V_{(BR)CBO}$	Collector-base breakdown voltage		$I_C=-0.5mA, I_E=0$	-200			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage		$I_E=-0.5mA, I_C=0$	-6			V
V_{CEsat}	Collector-emitter saturation voltage		$I_C=-500mA; I_B=-50mA$			-1.0	V
V_{BE}	Base-emitter on voltage		$I_C=-400mA; V_{CE}=-10V$			-1.0	V
I_{CBO}	Collector cut-off current		$V_{CB}=-200V; I_E=0$			-50	μA
I_{EBO}	Emitter cut-off current		$V_{EB}=-4V; I_C=0$			-50	μA
h_{FE-1}	DC current gain		$I_C=-150mA; V_{CE}=-10V$	60		240	
h_{FE-2}	DC current gain		$I_C=-400mA; V_{CE}=-10V$	50			

◆ h_{FE-1} Classifications

Q	P
60-140	100-240

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PACKAGE OUTLINE



Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)